VS-E7FX0212HM3

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LINKS TO ADDITIONAL RESOURCES



Application

PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 A				
V _R	1200 V				
V _F at I _F	1.60 V				
t _{rr}	45 ns				
T _J max.	175 °C				
Package	SMF (DO-219AB)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use as clamp, snubber and freewheeling diode in a flyback aux power supplies, bootstrap and desaturate for HV MOSFET and IGBT driver, high frequency rectifiers in a cuk and sepic circuit for LED lighting.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		1200	V		
Average rectified forward current	I _{F(AV)}	T _{Sp} = 85 °C, DC conduction	2	А		
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \text{ °C}, 8.3 \text{ ms}$ sine pulse	21	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	1200	-	-		
		I _F = 2 A	-	2.0	2.50	v	
Forward voltage, per diode	V _F	I _F = 2 A, T _J = 125 °C	-	1.70	1.95		
		I _F = 2 A, T _J = 150 °C	-	1.60	1.85		
Reverse leakage current, per diode	I _R	V _R = V _R rated	-	-	3		
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	30	μA	
Junction capacitance	CT	V _R = 1200 V	-	3.5	-	pF	

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COMPLIANT HALOGEN

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}$	A, I _{rr} = 0.25 A	-	35	45	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	105	-	ns
		T _J = 125 °C		-	145	-	
Peak recovery current		T _J = 25 °C	$I_F = 2 A,$ $dI_F/dt = 200 A/\mu s,$ $V_R = 800 V$	-	4.0	-	A nC
Peak recovery current	IRRM	T _J = 125 °C		-	5.0	-	
Reverse recovery charge	0	T _J = 25 °C		-	165	-	
neverse recovery charge	Q _{rr}	T _J = 125 °C		-	315	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	23	26	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with recommended pad size	-	125	-	°C/W
Approximate weight				0.015		g
Marking device		Case style SMF (DO-219AB)		М	SX	

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

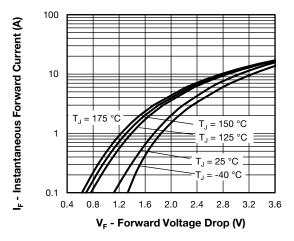


Fig. 1 - Typical Forward Voltage Drop Characteristics

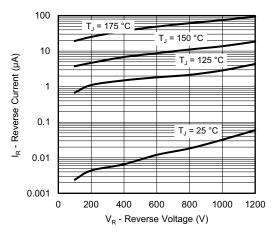


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



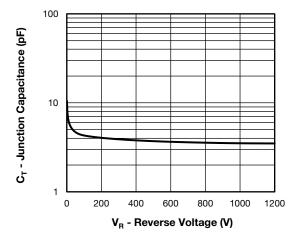


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

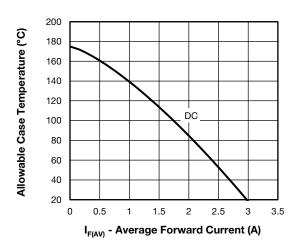


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

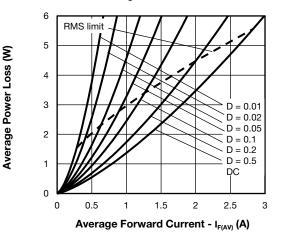


Fig. 5 - Forward Power Loss Characteristics

Note

 $\begin{array}{l} \mbox{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \mbox{forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 5)}; \\ Pd_{REV} = \mbox{inverse power loss} = V_{R1} \times I_R \mbox{ (1 - D)}; \mbox{ I}_R \mbox{ at } V_{R1} = \mbox{rated } V_R \mbox{ (see fig. 5)}; \end{array}$ (1)

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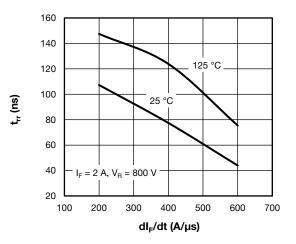


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

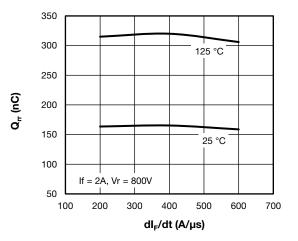


Fig. 7 - Typical Stored Charge vs. dl_F/dt

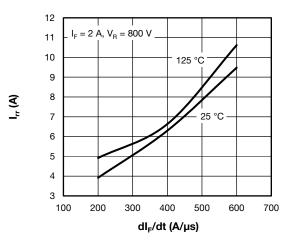
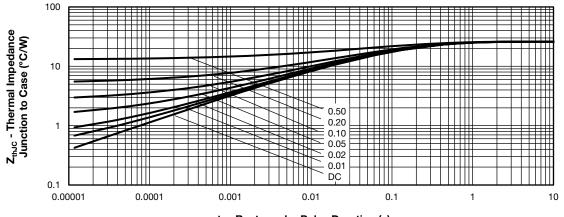


Fig. 8 - I_{rr} (A) vs. dI_F/dt

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t₁ - Rectangular Pulse Duration (s)

Fig. 9 - Transient Thermal Impedance, Junction to Case

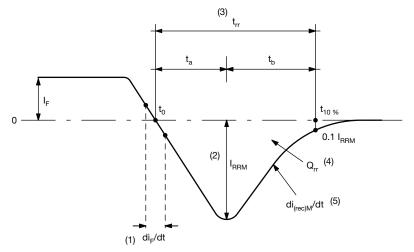


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

(1) di_F/dt - rate of change of current through zero crossing

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- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{0}^{t_{10\%}} I(t) dt$$

⁽⁵⁾ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

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ORDERING INFORMATION TABLE

Device code	VS-	E	7	F	x	02	12	н	М3
		2	3	4	5	6	7	8	9
	1	- Vish	iay Semi	conduct	ors prod	uct			
	2		cuit conf single c	iguratio diode	n:				
	3		•	generatio	on 7				
	4	- F=	SMF pa	ackage					
	5		cess typ hyperfa	oe, ist recov	very				
	6	- Cur	rent rati	ng (02 =	= 2 A)				
	7	- Vol	tage coo	de (12 =	1200 V)			
	8	- н=	AEC-Q	101 qua	lified				
	9	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lea

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-E7FX0212HM3/I	10 000	10 000	13"diameter plastic tape and reel			

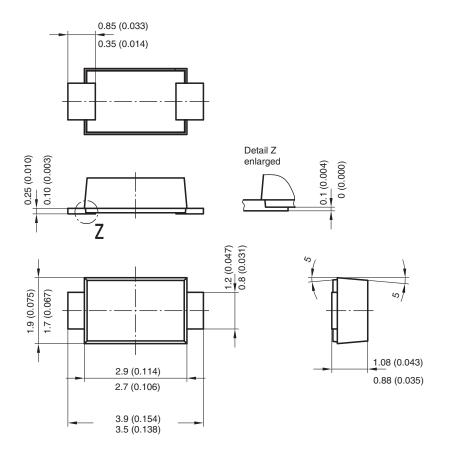
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				
SPICE model	www.vishay.com/doc?97265				



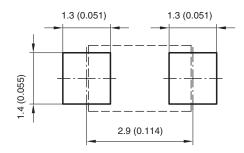
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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